

Radiation Damage in GaN/AlGaN and SiC Electronic and Photonic Devices

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The wide bandgap semiconductors SiC and GaN are commercialized for power electronics and for visible to UV light-emitting diodes in the case of the GaN/InGaN/AlGaN materials system. For power electronics applications, SiC metal - oxide-semiconductor field effect transistors (MOSFETs) and rectifiers and GaN/AlGaN HEMTs and vertical rectifiers provide more efficient switching at high power levels than do Si devices and are now being used in electric vehicles and their charging infrastructure. These devices also have applications in more electric aircraft and space missions where high temperatures and extreme environments are involved. In this review, their inherent radiation hardness, defined as the tolerance to total doses, is compared to Si devices. This is higher for the wide bandgap semiconductors, due in part to their larger threshold energies for creating defects (atomic bond strength) and more importantly due to their high rates of defect recombination. However, it is now increasingly recognized that heavy-ion induced catastrophic single-event burnout in SiC and GaN power devices commonly occurs at voltages ~50% of the rated values. The onset of ion-induced leakage

occurs above a critical power dissipation within the epitaxial regions at high linear energy transfer rates and high applied biases. The amount of power dissipated along the ion track determines the extent of the leakage current degradation. The net result is the carriers produced along the ion track undergo impact ionization and thermal runaway. Light-emitting devices do not suffer from this mechanism since they are forward-biased. Strain has also recently been identified as a parameter that affects radiation susceptibility of the wide bandgap devices.

I. INTRODUCTION

While Si high-voltage devices are still the most used components for power conversion, they have insufficient breakdown capabilities for many applications like power switching for the electricity grid [1-7]. Since the typical voltage range for power transmission is 100kV to 1.2 MV, this would require the serial stacking of large numbers of Si devices to achieve such high voltages. Even the voltages required for power distribution systems are in the range 4 to 100 kV, well beyond the capability of individual Si devices. As a result of their larger bandgaps ($>3\text{eV}$ compared to 1.1 eV for Si, these so-called wide bandgap (WBG) semiconductors, SiC and GaN, can achieve superior high-power switching performance than Si with much lower switching losses [1-4,6].

Both of these semiconductors have been commercialized for high power, high temperature electronics applications. They have significantly improved energy efficiency in power switching applications relative to Si devices [1-7]. They can also operate at higher temperatures. As an example, SiC devices and small-scale circuits have been shown to be capable of operation to 500°C , as part of the control systems needed for space exploration missions to Venus [8-11]. These WBG power switches have begun to replace Si in applications like electric vehicle power trains and charging systems because of their advantages in terms of higher current density, faster switching, near-zero reverse recovery time, lower drain-source on-resistance, improved temperature tolerance and smaller form factor [1-11]. The high-temperature capability is exploited in high temperature or harsh environments. Some examples include data logging when drilling during geothermal energy collection, turbines and sensing of gases in industrial

environments. SiC also has been suggested as a potential host for quantum qbits for quantum computers [12].

Some additional emerging markets for wide bandgap electronics include 5G infrastructure, renewable energy generation and data centers, where energy savings with more efficient electronics can be enormous [1-11]. In electric vehicles, the currently used 8 kHz Si power transistors in DC-to-AC traction inverters and on-board chargers are being replaced with 600-1200V SiC. To increase charging speed of battery packs in electric vehicles, the current 400-600V systems are expected to transition to 800-1200V [1-7]. At voltages beyond the transportation applications, SiC devices with $> 1,200$ V capabilities are expected to be used in for high-power solar farms and large three-phase grid converters [1-11]. GaN FETs are typically 600-900V devices for high-density converters with power > 10 kW for consumer, server, telecom and industrial power supplies grid converters [6,7]. The two technologies overlap at powers below 10 kW [5-7].

Another application for these SiC and GaN devices is in space-based satellite and defense systems not only for their high temperature capability but because they are more radiation-hard to displacement damage and total ionizing dose effects than Si [13-16].

2. Materials Properties of SiC and GaN

SiC has several crystal structures or polytypes [4,5], with the most common being 4H-SiC, 6H-SiC, and 3C-SiC. Both the 4H- and 6H-SiC polytypes have hexagonal crystal structures while 3C-SiC has a zinc-blende crystal structure. Table 1 compares the material properties of 4H-SiC with GaN and AlN, the two endpoints of the AlGaIn materials system. There are some noteworthy points from the Table, apart from the usual aspect of wide bandgap for high voltage and temperature operation. The wide band gap provides a transparent window range from the visible to mid infrared wavelengths. This contrasts with Si, which is transparent only in the infrared [6]. The thermal conductivity of SiC is second to diamond amongst dielectrics. SiC also has a large Youngs modulus, making it attractive for high frequency micro-mechanical devices. Divacancy point defects also form in SiC, With their relatively long spin coherence times, they are possible options in optical systems based on quantum effects [12]. Figure 1 shows a

spider diagram which compares the device attributes best suited to each material. Compared to Si, these are clearly high voltage, high temperature, high frequency applications for SiC and GaN.

With all the progress in crystal growth, device processing, packaging and thermal management, one of the only real disadvantages is still that the oxide/SiC interface has high defect densities compared to SiO₂ or other dielectrics on Si. These defects, such as dangling bonds and free and complexed carbon, limits the performance and reliability of SiC power MOSFETs by degrading the channel mobility and device reliability.

For GaN, it has the advantage of two different heterostructure systems, GaN/AlGaIn and GaN/InGaIn. The former is used for power electronics and UV LEDs, while the latter is used for visible LEDs. Bulk GaN substrates are available but still are expensive and variable in quality, so it is common to grow epitaxial layers of GaN on substrates such as SiC, Si or sapphire. Thick epitaxial layers are also still under development for achieving high breakdown (>20 kV) rectifiers.

Table I. Summary of properties for SiC, GaN and AlN. The various figures of merit for each material are normalized to Si ⁽⁴⁻⁷⁾

Parameter	AlN	4H-SiC	GaN
Bandgap (eV)	6.0	3.25	3.4
Dielectric Constant	9.8	9.7	9
Breakdown Field (MV.cm ⁻¹)	15	2.5	3.3
Electron Mobility (cm ² /V.s)	400	1000	1250
m _e /m _o	0.31	0.39	0.20
m _h /m _o	0.42	0.82	1.00
Saturation velocity(10 ⁷ cm/s)	1.2	2	2.5

Thermal Conductivity (W/mK)	320	490	230
Bulk modulus (GPa)	190	700	290
Moh's hardness	7	9.3	~6
Surface Hardness (GPa)	14	30	12
Density (g.cm ⁻³)	N	N	N
Doping capability	high P low	med P high	high P low
E _D (meV)	90	60	25
E _A (meV)	500	250	170
Substrate size (mm)	50	150	100
T _s (°C)	3000	2800	2500

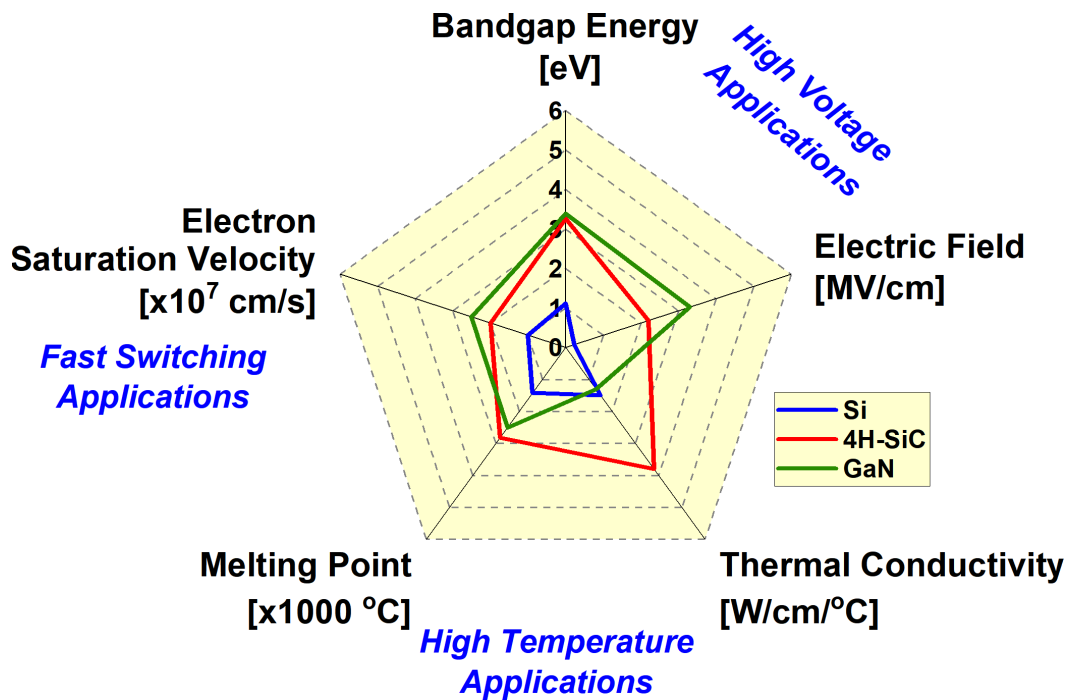


Figure 1. Spider diagram of relative advantages of SiC and GaN over Si in device applications.

3. Summary of Radiation Effects

It is widely accepted that SiC and GaN devices have high inherent resistance to total dose radiation effects but are less robust against transient radiation effects [17-37]. The latter are classed under single-event effects (SEE) and are important in space environments. In space, the radiation comes from three sources, namely (i) solar flares, (ii) trapped protons or electrons in the Van Allen radiation belts and (iii) galactic cosmic rays (GCR). For solar flares and the trapped radiation, protons have energies from keV-500 MeV while the electron energy ranges are from eV - 10 MeV [38-45]. The GCR originate from sources outside our solar system and are predominantly protons (90%) and heavier elements spanning the periodic table but with much lower fluxes for the heavier ions. The energy range of cosmic rays reaches the TeV region, again with much lower fluxes as energy increases. In the past 40 years, there have only been 22 events with energies beyond 10^{20} eV. These are referred to as super-Greisen-Zatsepin-Kuzmin occurrences. This corresponds to a flux of one event per km² per century.

An important parameter is the energy required to create an electron hole pair, E_i in a semiconductor. The most accepted empirical relation is [46-54]

$$E_i = 2.8E_g + 0.6eV$$

For GaN, this corresponds to 10.1 eV or $\sim 2.5 \times 10^{12}$ e/h pairs per rad.cm³. For 4H- SiC, the value is 9.65 eV or 2.6×10^{13} e/h pair per rad.cm³. For AlN, this corresponds to 17.4 eV or 1.45×10^{12} e/h pair per rad.cm³. In terms of relative energy deposition, the NIEL or energy that goes into displacements is about 0.1% of the total energy loss [32-37]. The vast majority goes into electronic energy loss mechanisms such as ionization, e-h pair production and phonon creation.

For devices, the three different radiation effects are relevant- single event effects (SEE), total ionizing dose (TID) and displacement damage (DD). It is common to treat SEEs separately since they result from interactions of a single energetic particle. By contrast, TID and DD are cumulative effects related to the ionizing dose and the particle fluence, respectively [17-25]. Total Ionizing Dose (TID) is a result of ionizing radiation inducing excess charge in the dielectric layers used in MOS devices. When such a MOS device is irradiated, large numbers of e-h pairs are created in the dielectric according to the relation discussed earlier. When the oxide is under bias, the electrons which do not recombine drift to the contacts. The time scale for this is short, on the order of

picoseconds. In all oxides, holes have much lower mobility than the electrons and for positive bias during the radiation exposure, they drift to the semiconductor /dielectric interface, where some become trapped at defects [14,16]. This trapping induces a positive charge built-up in the dielectric, which screens the applied bias and alters the electric field in the semiconductor. The trapped charge is apparent as a shift of device threshold voltage. Thus, TID affects mainly devices with MOS or MIS gates. Finally, displacement damage is displacement of lattice atoms from their original substitutional positions by nuclear scattering, fission and nuclear reactions. These point defects generally create new energy levels in the bandgap, which act as carrier traps and reduce carrier mobility. These changes manifest as a degradation in device dc and ac performance.

Single Event Effects (SEE) are due to single energetic particles. The passage of such ions may cause transient errors, which include Single Event Upset (SEU) and Single Event Transient (SET). They may also cause so-called hard errors. These include Single Event Latch-up (SEL). Single Event Gate Rupture (SEGR) and Single Event Burnout (SEB) [31-37]. Figure 2 shows a schematic of the three different types of radiation damage created in semiconductor devices.

The WBG materials are more radiation-hard than Si because of their stronger atomic bonding. This reduces the density of point defects created per unit energy of ionizing radiation. However, this is not enough to explain the empirical differences in carrier removal rates between GaN, SiC and Si. The former two have a much higher degree of dynamic annealing that occurs during the irradiation. If one employs as a figure of comparison the carrier removal rate in these materials relative to that number in Si, then a reasonable estimate is that GaN and SiC are at least 1-2 orders of magnitude less susceptible to defect creation (displacement damage) by radiation exposure [17-37].

In terms of the effects produced by different types of radiation, photons (gamma rays and x-rays) and neutrons primarily produce ionization effects and displacement damage, respectively. Neutrons can produce Gossick zones, which are regions of dense lattice disorder surrounded by relatively defect-free areas. This has complicated effects on devices and the spatial location of the high damage regions within the depletion region is important. High energy photons may create displacement damage by the Compton

mechanism. Neutrons can initiate nuclear reactions which produce secondary particles, such as photons. In turn, these create ionization in the semiconductor [13-16].

Charged particles such as protons and alpha particles produce both displacement and ionization damage. When traversing a semiconductor device, they experience Coulombic interactions with the electrons in the elements comprising the semiconductor, which reduces their energy along the ion track. For low energies in the range of keV, Coulombic collisions with the atoms in the semiconductor are the main energy loss mechanism [53-65]. In terms of relevant doses, the current defense system requirements for TID is 300 krad (Si), SEU is 10^{-10} errors/bit-day, SEFI 10^{-5} errors/chip-day, DR Upset $>10^8$ rad (Si)/s and displacement damage 10^{12} n/cm².

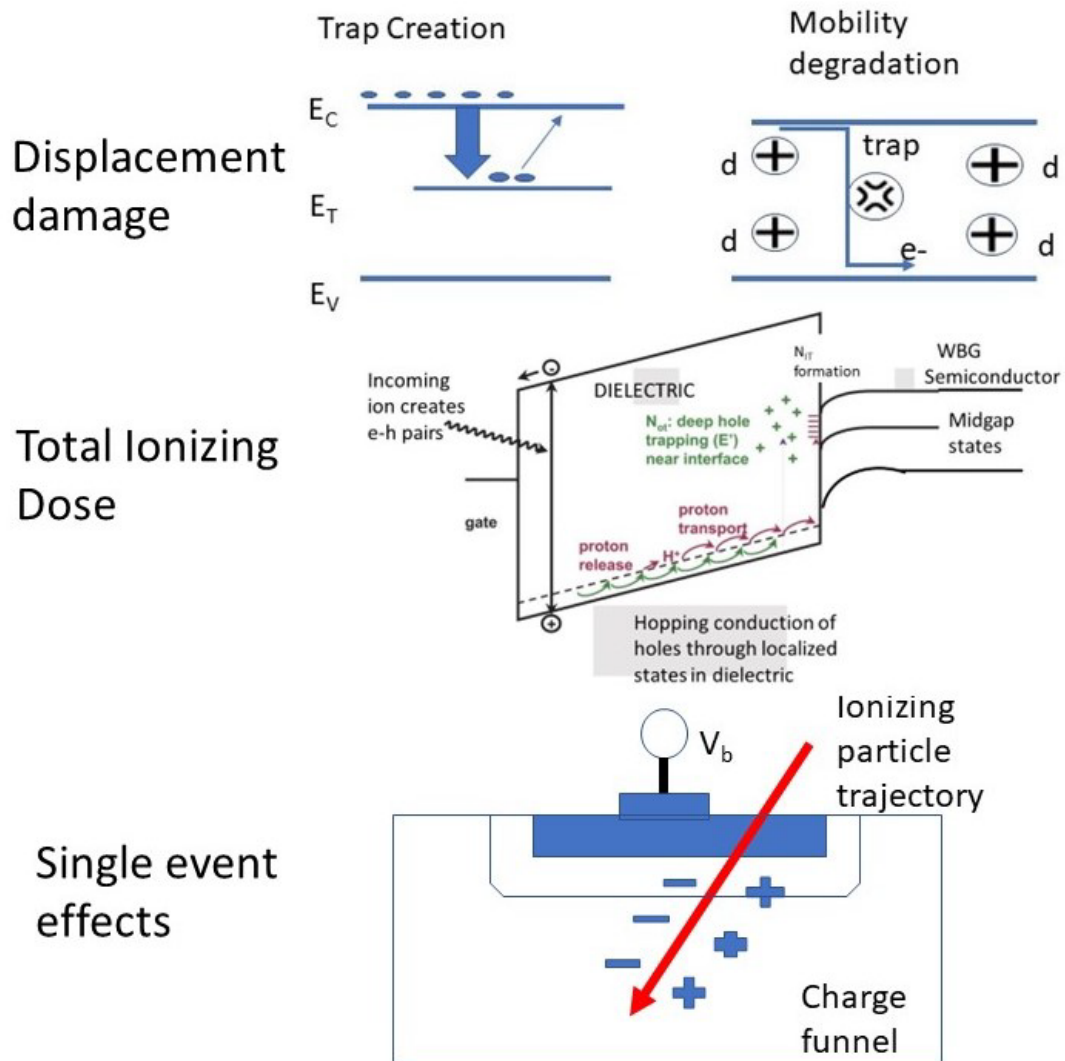


Figure 2. Schematic of radiation effects in semiconductors.

The magnitude of defect production and the resultant damage accumulation depend on the relative energy lost to electronic energy loss (S_e) or nuclear energy loss (S_n) [17-39]. The interplay between these can be complex, producing additive, competitive or synergistic effects on how the damage evolves. The electronic stopping power is also known as the inelastic linear energy transfer (LET) to the semiconductor. The ionization produced by this energy loss consists of creation of e-h pairs on a femtosecond time scale. This produces a local thermal spike around the ion track through electron-phonon coupling to the atomic structure on the timescale of a few hundred femtoseconds. The localized energy deposition can exceed the bond strength of the semiconductor lattice, even leading to localized melting [17-39].

At high LET values, the ion tracks are readily visible by transmission electron microscopy. Depending on the atomic number of the ion and its LET, the tracks may be several microns long with diameter of 5-10 nm. An example is shown for GaN irradiated with Pb in Figure 3 [35], showing both images of the tracks and a histogram of track sizes. GaN ion tracks may contain amorphous material within the track. However, there is a strong tendency for recrystallization. In the case of AlN, it is difficult to detect ion track formation because of an even stronger recrystallization effect [22,23,35-39]. These effects are also seen in molecular dynamics simulations [30,33]. An example is shown in Figure 4. The physics behind the model is based on excited electrons transferring energy to lattice atoms through electron-phonon coupling. This produces the localized transient lattice heating. At sufficiently high LET, the semiconductor along the ion path melts [30,31,33]. The high temperature in the center of the ion track is subsequently reduced by phonon production or heat conduction by free electrons. Due to athermal defect recombination, the damage production is typically much lower than that given by the simple estimates of the defect concentration given by the nuclear stopping divided by the damage threshold energy [30,31,33]. In the case of ion tracks in GaN, the simulations suggest that N₂ bubbles form within the track. These are shown as dark contrast regions in the tracks of Figure 4.

For the nuclear stopping mechanism, the incoming ion and the recoiled atoms undergo a series of additional collisions with the lattice atoms. Energy is lost in each of

these interactions [32,36, 53-65]. At low ion fluences (between 10^{10} - 10^{12} ions/cm², depending on ion energy and mass), the damage regions from individual ions do not overlap. The nuclear stopping power is the average energy loss per unit path length. As the incoming ion initially enters the semiconductor, the energy imparted to recoils is high. Therefore, the recoiled atoms can also displace atoms, producing a collision cascade [63-73]. The threshold energy for atom displacement is defined as the smallest kinetic energy required to displace an atom from its substitutional lattice site [74-94]. If the semiconductor crystal has anisotropic symmetry, the displacement thresholds will also be anisotropic [53-62]. In GaN, there is a large difference between the masses of the elements, so an asymmetry in the damage between Ga and N occurs. Experimentally, the average threshold is 41 eV for the Ga sublattice [36,37,75]. Molecular dynamics simulations gave average thresholds of 45 and 110 eV for Ga and N, respectively [36,38], while other estimates gave predicted displacement energies of 109 eV for N and 34 eV for Ga). It is difficult to measure these thresholds and there is significant scatter in the reported data. The thresholds for Si are $T_d = 12.9$ eV and $T_d = 21$ eV [32,33]. Horita et al. [58] reported an experimental value for N displacement in GaN as 21.8 eV. These experiments were carried out at irradiation energies were selected to displace only nitrogen atoms. There were two electron traps detected, labelled EE1 (0.13 eV) and EE2 (0.98 eV). These were assigned to nitrogen vacancies $V_N (+/0)$ and nitrogen interstitials $N_I (0/-)$, respectively [95].

Damage is more significant at low temperatures due to reduced mobility of point defects. At elevated temperatures, however, the dynamic annealing of point defects may actually prevent semiconductors do not amorphization of the lattice [32,54]. The critical temperature for such prevention of amorphization is a few hundred degrees.

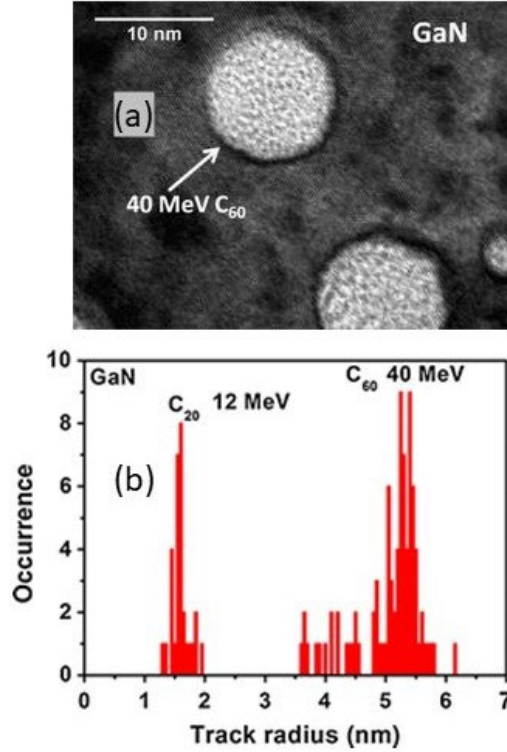


Figure 3 (a). High resolution plan view-TEM of GaN irradiated with 40 MeV C_{60} ($S_e = 59 \text{ keV nm}^{-1}$, $10^{11} \text{ ions cm}^{-2}$) (b) Histogram of track sizes in GaN simultaneously irradiated with 40 MeV C_{60} ($S_e = 59 \text{ keV nm}^{-1}$) and 12 MeV C_{20} ($S_e = 19 \text{ keV nm}^{-1}$). Reprinted with permission from J Mater Sci **50**, 5214 (2015). Copyright 2010 Springer.

As they lose energy to both nuclear and electronic stopping processes, the incoming ions eventually slow to thermal velocities ($< 1 \text{ eV}$). The two stopping processes are almost completely independent of each other. There can also a dependence of damage accumulation on the chemical nature of the incoming ions. GaN shows complete amorphization for pre-implantation with fluorine, in sharp contrast to pre-implantation with neon, phosphorus or argon, which reduce damage [37],

Depending on device bias voltage and the ion energy and LET, the passage of an ion can lead perturbations in internal electric fields within the device that are larger than the critical field for avalanche breakdown.

A final point is that the passage of ionizing radiation can alter the diffusivity of point defects in semiconductors [97-99]. The migration energy for ionized defects is generally lower than for non-ionized defects. This can produce ionization-stimulated diffusion of point defects and impurities. The Bourgoin mechanism is the athermal recombination of

point defects [99]. This obviously reduces the effective defect production. This mechanism has been observed for SiC [21,23,25]

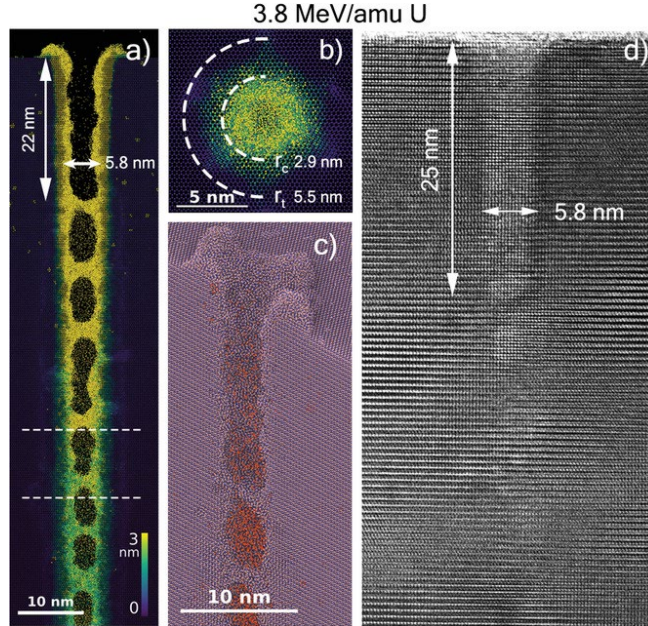


Figure 4. Simulated a) cross-sectional, b) plan-view images and c) 3D of a track produced by a 3.8 MeV amu^{-1} U ion ($\epsilon_e = 55.15 \text{ keV nm}^{-1}$). The orange balls in (c) represent N_2 molecules. d) Experimental TEM cross-sectional image of a track produced by the same U ion. The dashed lines in (a) indicate the region from which the image in (b) was taken. The simulated and experimental track morphologies are in excellent agreement. Reprinted with permission from Small, 18, 2270265 (2022). Copyright (2022) under a Creative Commons License.

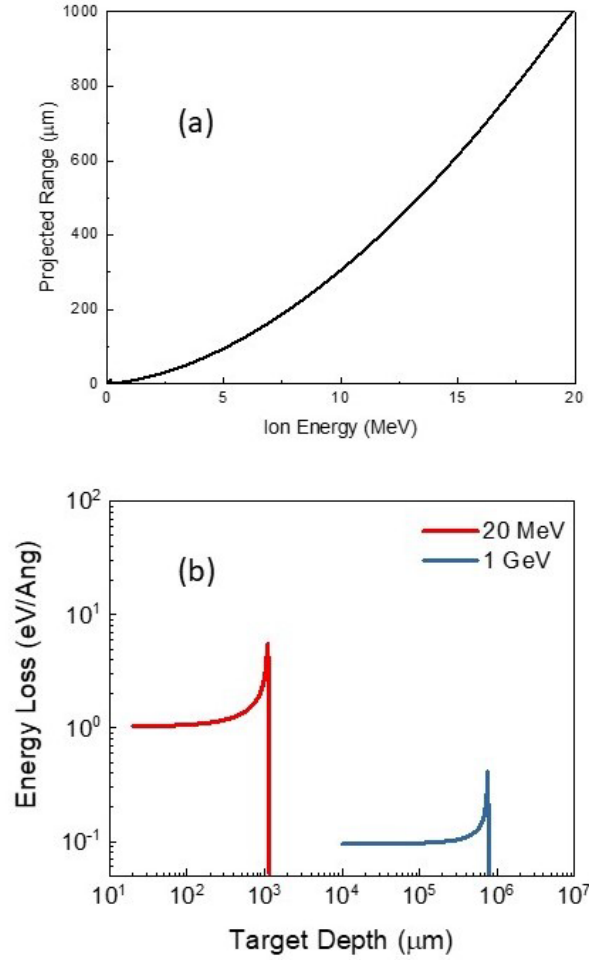


Figure 5.(a) Range of high energy protons in GaN and (b) energy loss vs depth for 20 MeV protons, dose 10^{14} cm^{-2} and 1 GeV, dose $4 \times 10^{13} \text{ cm}^{-2}$ protons in GaN .

4. GaN HEMTs and Vertical Rectifiers

As pointed out previously, since most GaN-based devices use metal-gates, they do not suffer from oxide damage effects and are tolerant to total ionizing radiation dose effects [100,101]. Figure 5 shows the projected range of high energy protons in GaN (top) and energy loss vs depth for 20 MeV protons, dose 10^{14} cm^{-2} and 1 GeV, dose $4 \times 10^{13} \text{ cm}^{-2}$ protons in GaN (bottom). Note that at 20 MeV, the range is $\sim 10^3$ microns, larger than the thickness of the HEMT structure.

Proton damage for ions $> 2 \text{ MeV}$ energy is only apparent for doses $> 10^{14} \text{ cm}^{-2}$. This is equivalent to hundreds of years in low earth orbit. Significant annealing of damage

occurs after 500°C annealing [102,103]. Similar results are reported for alpha particles, while electrons were less damaging than either of these other ions.

For gamma ray irradiation of GaN HEMTs, post-irradiation annealing at 200 °C caused some restoration of parameters such as diffusion length, drain current and transconductance [104-117]. A comparison of the carrier removal rates for different types of radiation in GaN, as a function of energy in Figure 6 shows protons are the most damaging, followed by neutrons, electrons and gamma rays [2]. Heavy ion irradiation with > 1 GeV Bi or Xe ions at doses > 10^{11} cm⁻² caused large reductions in device source-drain current [118-122].

Figure 7 shows the deterioration of dc performance of GaN HEMTs after 10 MeV proton damage at a fluence of 10^{14} cm⁻². The drain I-V characteristics (a) and transfer characteristics (b) from the HEMTs show reduced current by 20-50% [120-132]. For 10 MeV irradiated HEMTs, saturation drain current at $V_G=0$ V was reduced by 24%. Figure 7 (b) shows transfer characteristics after irradiation. The extrinsic transconductance, gm, was reduced by 22% and the threshold voltage showed a positive shift of 0.34 V. The ion bombardment reduces carrier density and electron mobility [2,120-133]. Larger degradation of the gm and larger V_{th} shift were obtained for lower proton energies. This corresponds to a higher level of NIEL in the 2D electron gas. SRIM data indicate most of the nuclear stopping damage occurs well into the substrate, at depths of 105, 335 or 672 μm for 5, 10 or 15 MeV, respectively. The two-dimensional electron gas channel (2DEG) of the HEMT is 22 nm below the surface, where the vacancy densities are several orders lower than at the damage peak. For the higher proton energies, there is lower amounts of displacement damage around the 2DEG. Therefore, 5 MeV protons should degrade the HEMT more severely as compared with 10 or 15 MeV protons.

Worsening of GaN HEMTs performance occurs at DD levels greater than encountered in most space applications. As shown in Figure 8 [109] there is a 10x improved performance of GaN compared to GaAs HEMTs in terms of resistance to degradation by irradiation. The susceptibility to displacement damage is larger when devices are biased during irradiation or have had prior hot-carrier stress [134,135]. There are fewer studies of GaN HEMT TID effects, which appear to be a strong function of gate design. In depletion mode Schottky gate devices Aktas et al. [65] reported a 0.1 V

threshold shift after 6 Mrad (Si) γ irradiation. For enhancement mode, p-GaN gate HEMTs, there was no significant shift after 15 Mrad (Si) proton irradiation [133,134]. For 500 krad (Si) γ irradiation, there was < 18% V_{th} shift [110].

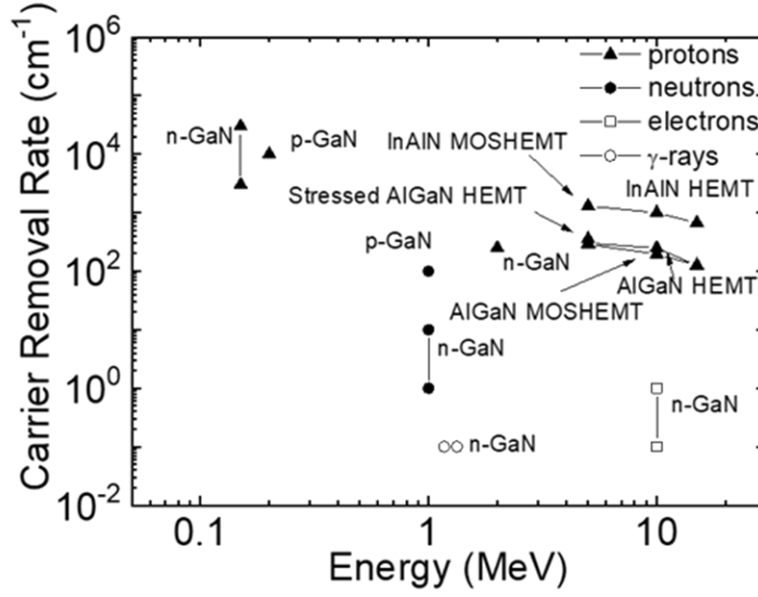


Figure 6. Compilation of carrier removal rates in GaN-based materials and devices as a function of radiation type and energy.

For irradiation with heavier ions, it is important to calculate the NIEL and ionization loss in the 2DEG region. An example of a typical power HEMT structure is shown in Figure 9. Since the 2DEG is so close to the surface, heavy ions can create significant damage, as well as create secondary recoil ions that also damage the channel of the HEMT. SRIM simulations of the ionization loss by primary ions and their recoils are shown in Figure 10 (a) while the vacancy concentrations created by the NIEL of the ions and recoils are shown in Figure 10(b). The SRIM program calculates the ion penetration as a series of independent binary collisions.

Additional temperature-dependent transport measurements of minority carrier lifetime and diffusion length have been reported. Typically, these require the samples to be wire-bonded for electron beam-induced current (EBIC) to measure minority carrier transport properties, as shown in Figure 11 (a) and (b). Lee et al. [116] reported dose-dependent effects in AlGaIn/GaN HEMTs exposed to ^{60}Co gamma radiation. For doses

below ~ 250 Gy, the minority carrier diffusion length in the HEMTs increased 40%. Similarly, there was an increase in transconductance and reduced gate leakage current after low doses. For doses above ~ 300 Gy, the performance of HEMTs deteriorated, due to the onset of increased carrier scattering from radiation-induced defects.

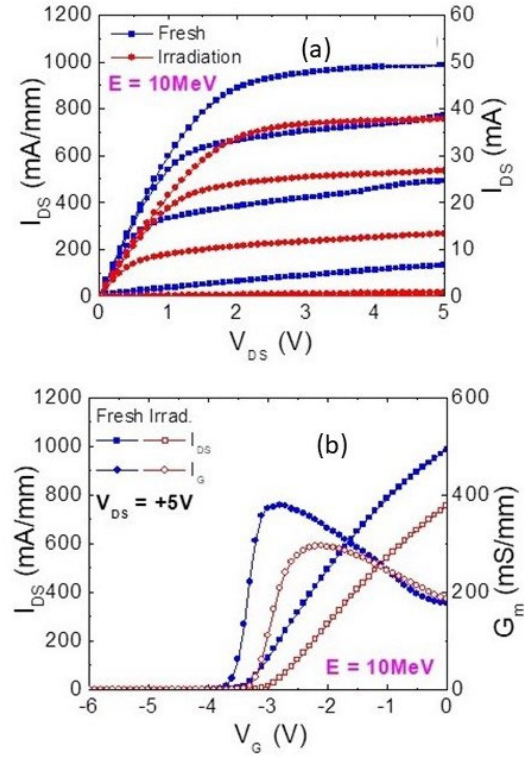


Figure 7. Drain I-V characteristics (a) and transfer characteristics (b) from GaN HEMTs before and after 10 MeV proton irradiation. Reprinted with permission from J. Vac. Sci. Technol. B **31**, 042202 (2013), copyright 2013 American Vacuum Society.

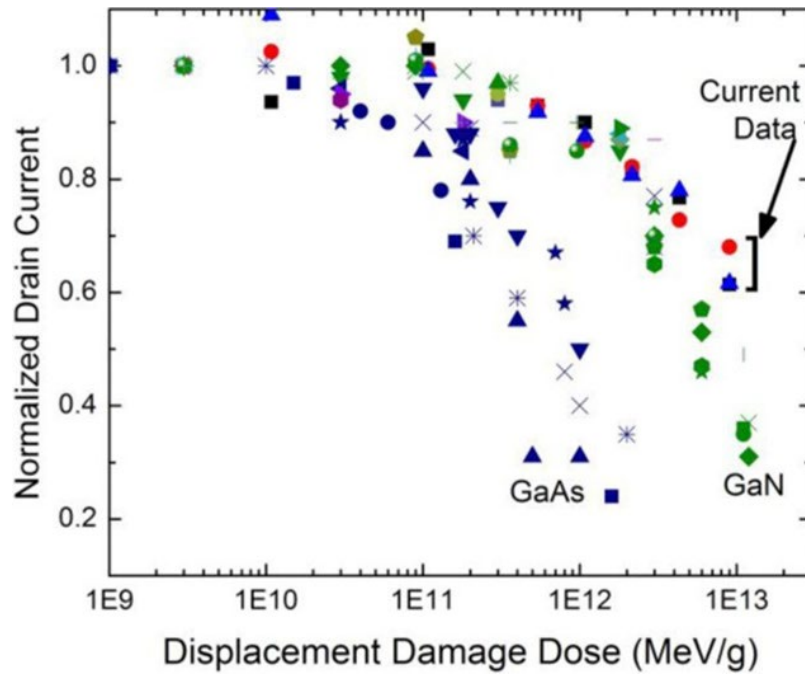


Figure 8. Degradation of normalized drain current of GaN HEMTs compared to their GaAs counterparts. Reproduced with permission from ECS J. Solid State SC. 5, Q208 (2016). Copyright (2016) under a Creative Commons License.

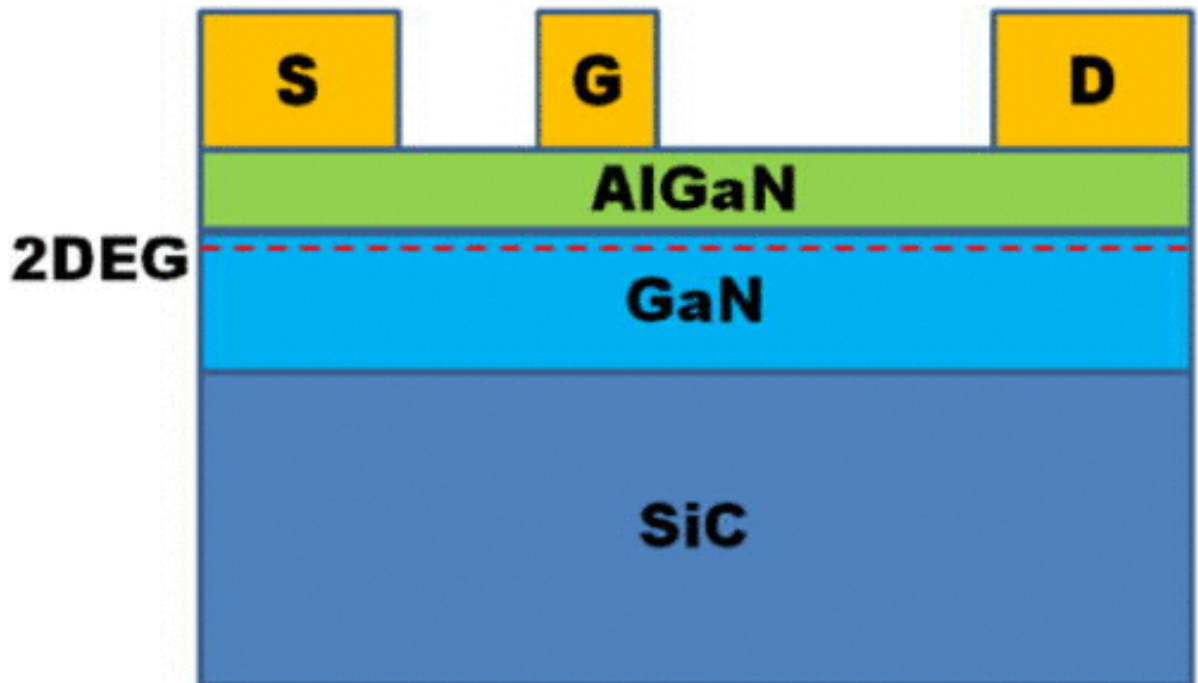


Figure 9. Schematic of typical high power GaN HEMT. These are typically grown on SiC substrates to improve the thermal characteristics. A typical thickness of the AlGaN donor layer is 25 nm and the GaN buffer is 3-5 μm .

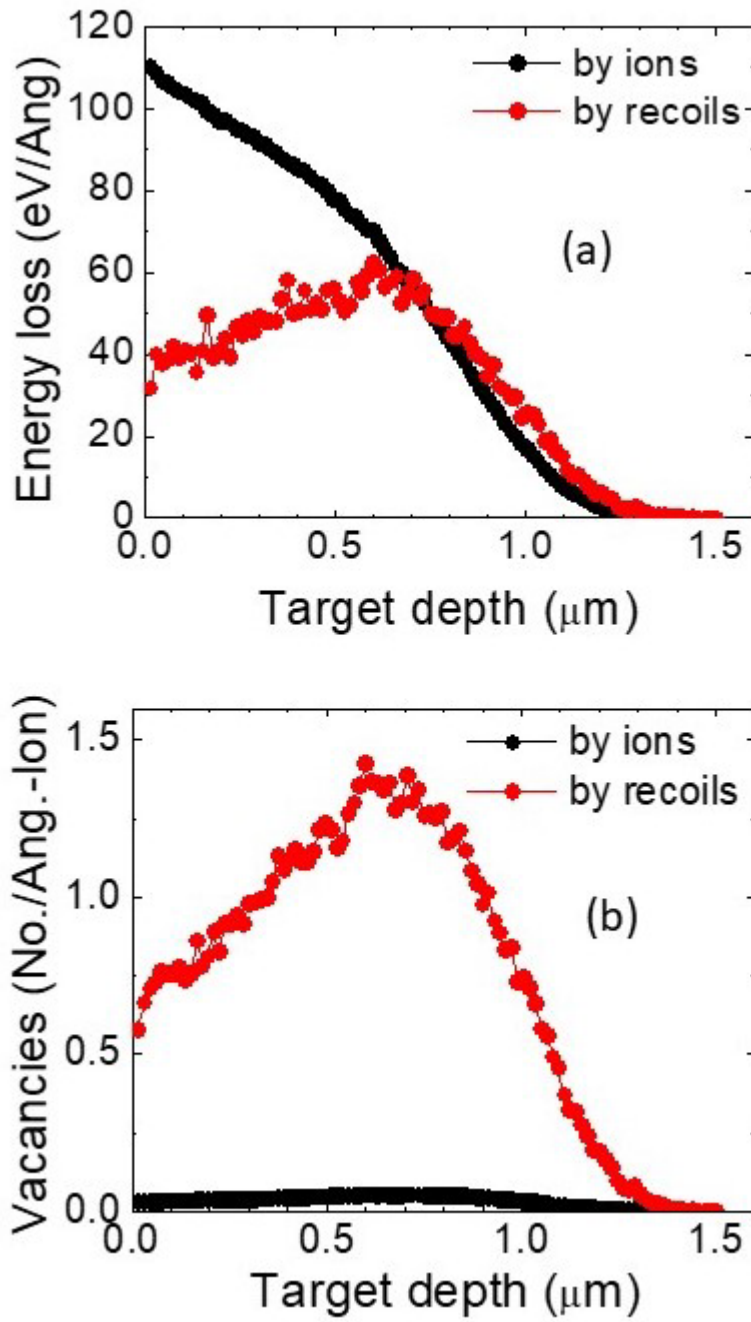


Figure 10. SRIM simulations of ionization energy loss (a) created by 2 MeV Ge^+ ions and the recoils they created in a power GaN HEMT structure. The ion projected range is $\sim 0.8 \mu\text{m}$. The number of vacancies created by the NIEL of the primary ions and the recoils created are shown in (b).

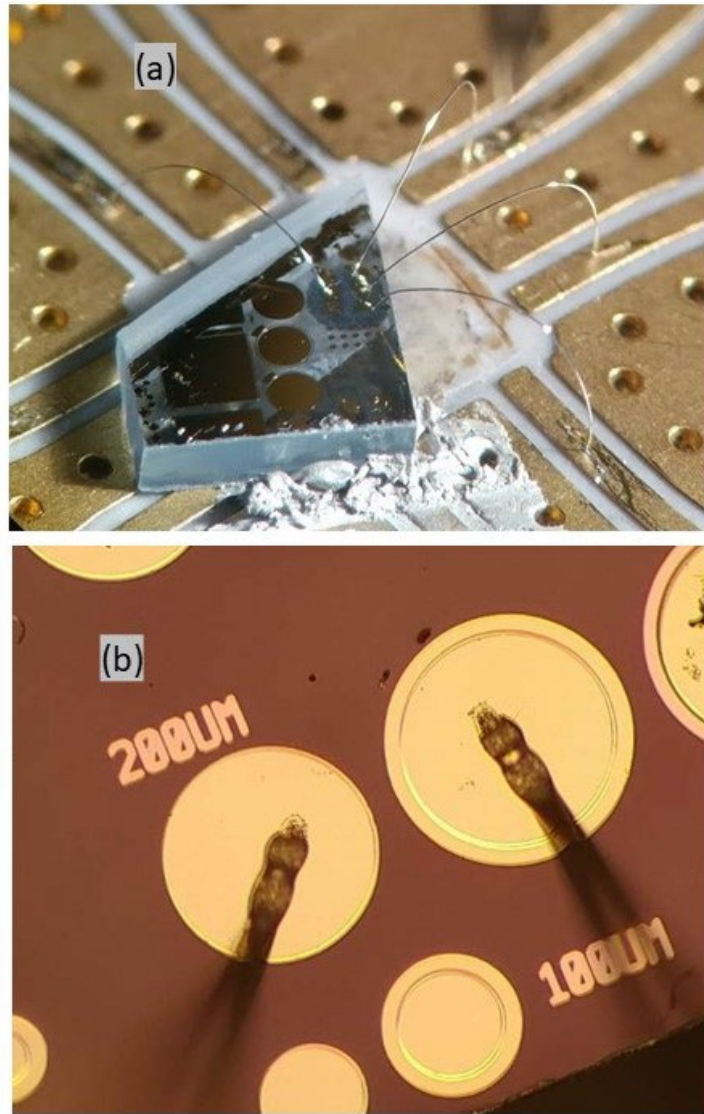


Figure 11. Optical images (a) and SEM images (b) of wire bonded GaN HEMTs for transport measurements.

Figure 12 shows a schematic of the two main degradation mechanisms induced in GaN HEMTs by radiation [2]. The first is creation of midgap trap states which reduces 2DEG density and drain current. These states are typically charged, which reduces the electron mobility by carrier scattering.

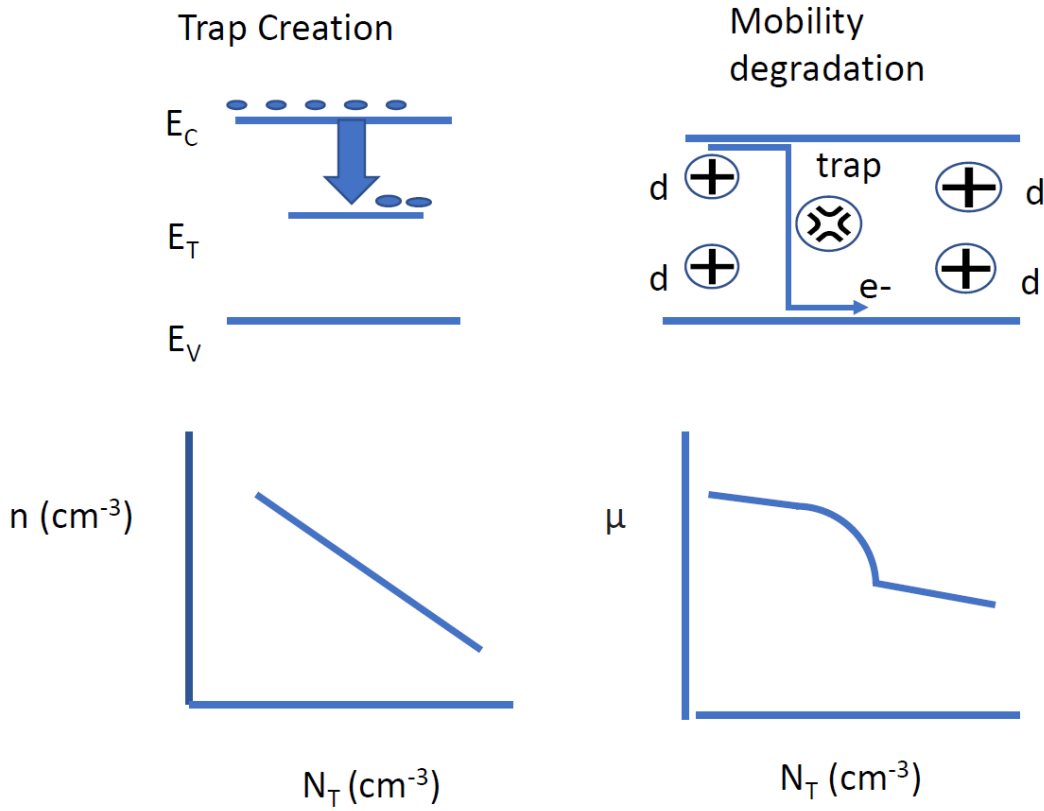


Figure 12. Schematic of main degradation mechanisms in GaN HEMTs exposed to radiation. The displacement damage created midgap states that trap carriers and reduce carrier mobility.

For GaN quasi-vertical p-i-n rectifiers, irradiation with 150 keV protons reduced both carrier concentration and mobility of p-GaN and n-GaN [1305]. At a proton fluence of 10^{15} p/cm², the p-GaN became highly resistive n-GaN. The p-GaN Ohmic contact converted to rectifying behavior and the main reverse leakage mechanism switched from space-charge-limited current conduction to Ohmic conduction [135].

Aoshima et al. [95] reported a correlation between NIEL and production rates of electron traps at $E_C - (0.12-0.20)$ eV for irradiation of GaN. As shown in Figure 13, the correlation indicates the trap states are generated by atomic displacements.

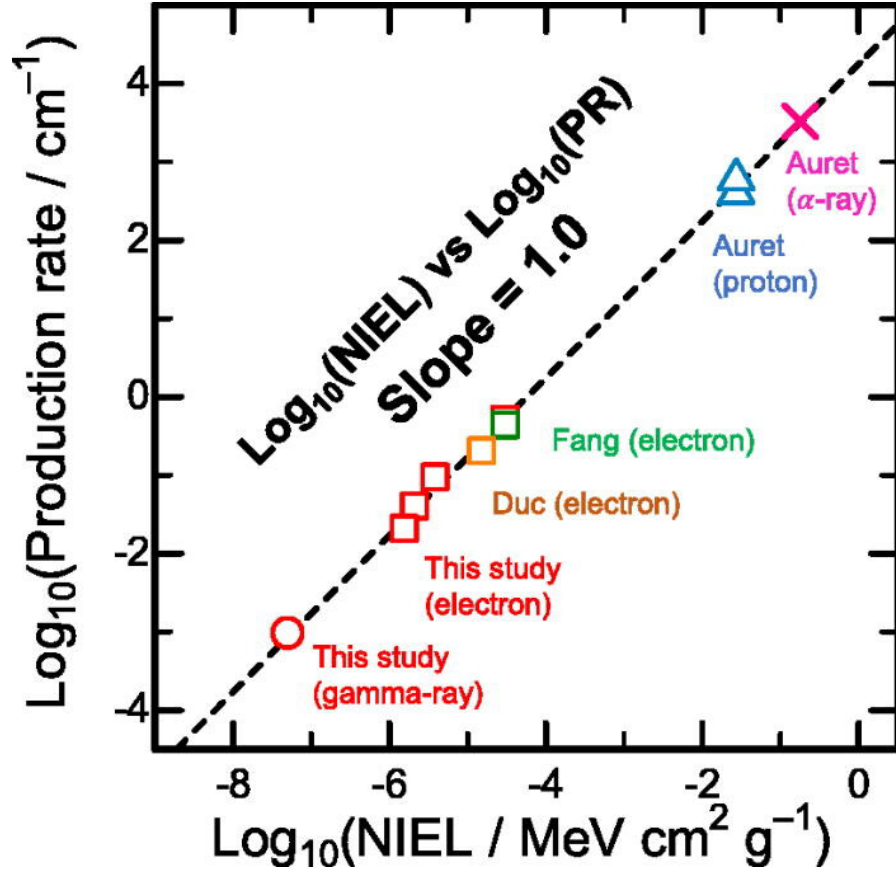


Figure 13. Production rates of electron traps at $E_C - (0.12-0.20)$ eV as a function of NIEL for electrons, protons, α -rays, and gamma-rays. Reprinted with permission from Appl. Phys. Lett. **122**, 012106 (2023). Copyright 2023, American Institute of Physics.

Rasel et al.[104-107] recently reported in gamma-irradiated HEMTs that localized regions under tensile stress exhibited higher radiation-induced strain. Co-60 γ -rays have a large mean free path in GaN, as shown in Figure 14. The gamma rays create damage throughout the entire HEMT structure. The suggested mechanism for their observations was a dependence of the carrier concentration and mobility in the 2DEG on the tensile stress in the device. When HEMTs were electrically pre-stressed prior to irradiation, they exhibited larger threshold voltage shift and a 100x increase in leakage current. In addition, with saturation current was lowered after irradiation, as shown in Figure 15. The high electric fields during stressing change the strain in the system and can lead to creation of defects. This was supported by locally relieving strain by creating micro-trenches underneath the channel. These reduce the strain within device, which reduces

2DEG density and mobility. This strain relaxation also reduced the radiation damage created by 10 Mrads (SiO_2) of ^{60}Co -gamma exposure.

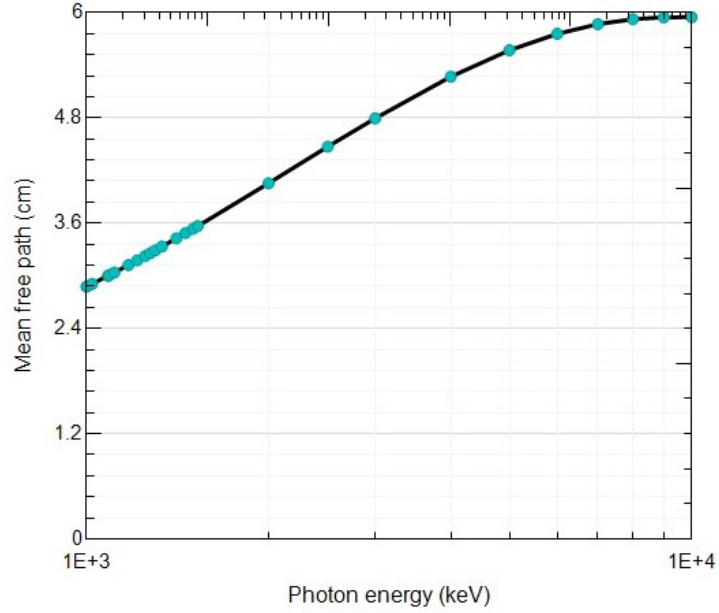


Figure 14. Mean free path of gamma rays in GaN as a function of energy. The plot was calculated from the code in Rad Phys Chem,**182**, 109331 (2021)

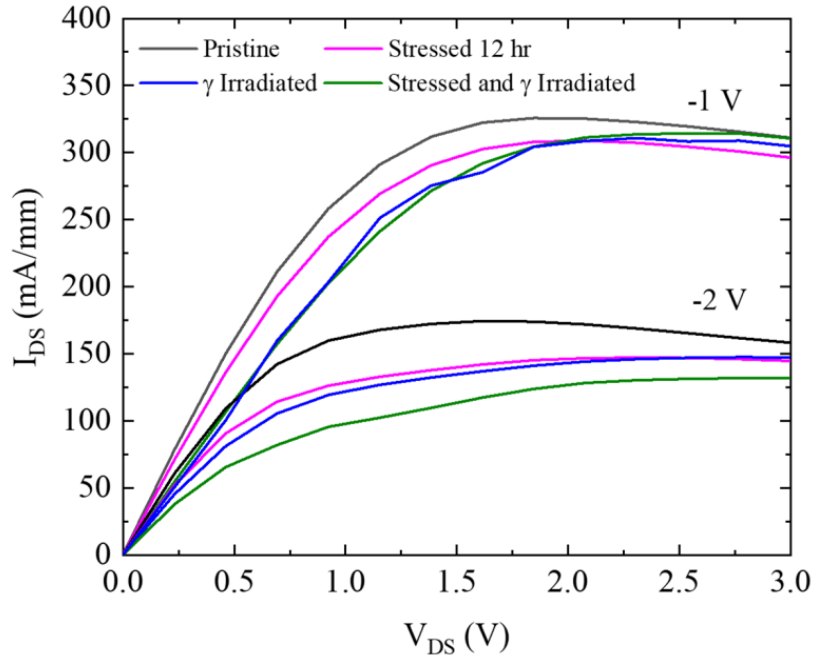


Figure 15. Effect of gamma irradiation on the forward I-V curve for zero gate voltage at different device conditions. Reprinted with permission from Appl. Phys. Lett. **120**, 124101 (2022), Copyright 2022 American Institute of Physics.

Rasel et al.[104, 105] also demonstrated a novel non-thermal annealing process for gamma-induced damage in GaN HEMTs, using the electron momentum from short, high current density pulses to anneal defects. This process was used on 5 Mrad dose (SiO_2) irradiated HEMTs and restored saturation current and maximum transconductance while threshold voltage was partially recovered. By sharp contrast, conventional thermal annealing at 300 °C degraded the irradiated device characteristics.

The susceptibility for SEE in GaN HEMTs increase with voltage [108]. SEB in ~ 600 V p-gate parts occurs at ~50% of rating at LET ~ 40 MeV.cm²/mg (Si). The burnout occurs at insulators for source or gate field plates. GaN HEMTs have several catastrophic SEE failure modes. Figure 16 shows single event burnout in Xe irradiated HEMTs at 380V bias [1038]. The first failure mode was creation of a leakage path from drain to Si substrate through the buffer layer. The other mode was damage between the drain and source. In these experiments, the damage was produced by ions with LET ≥ 30.6 MeV/(mg/cm²) at normal incidence.

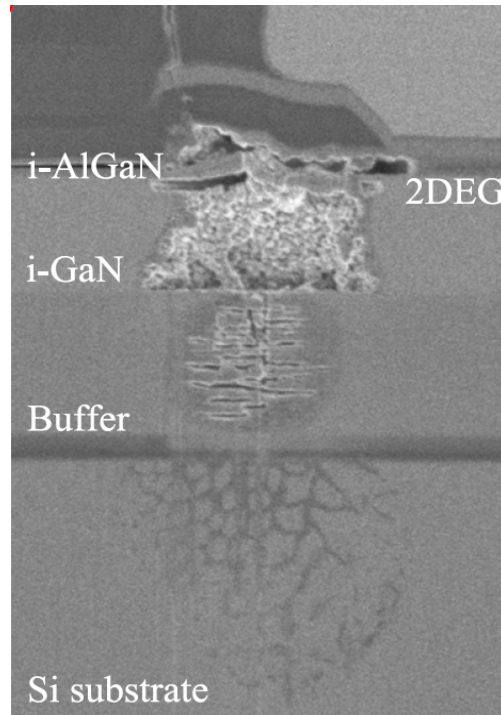


Figure 16. Heavy ion induced single event burnout in GaN/AlGaN HEMT. The device was damaged during Xe ion irradiation at $V_{DS}=380$ V. Reprinted with permission from IEEE T. Nucl Sci, **65**, 1956 (2018). Copyright 2018 IEEE.

5. GaN Photonic Devices

GaN-based light-emitting diodes (LEDs) and laser diodes are commercialized for the UV-visible range, using GaN/InGaN for the green/blue region of the spectrum and GaN/AlGaN heterostructures for the UV. These devices operate in forward bias, to drive electrons and holes from either side of a p-n junction together to recombine and emit photons whose wavelength is determined by the bandgap of the active region. Radiation induced defects act as both carrier trap states and recombination centers, enhancing nonradiative recombination and reducing carrier concentration [135-142]. The domination of such processes over radiative spontaneous and stimulated emission degrades LED or laser performance. Osiński et al. [143] reported improved radiation hardness of nitride-based LEDs relative to GaAs LEDs. The output power of AlGaIn/InGaIn/GaN green LEDs after 2 MeV protons at 10^{12} cm^{-2} decreased 40%. Gaudreau et al. [144] reported 2 MeV protons at $> 3 \times 10^{12} \text{ cm}^{-2}$ reduced both electrical and optical performance of AlGaIn/ InGaIn/ AlGaIn blue LEDs, with light output reduced by more than 99% for 10^{15} cm^{-2} proton fluence. The optical properties were observed to be degraded at a faster rate than that of the electrical properties. This was a result of the higher nonradiative transitions caused by the presence of radiation-induced defect states. Khanna *et al.* [145] reported the proton energy dependence of light output degradation of blue LEDs over the range 2–115 MeV.

The effects of proton irradiation on InGaIn/GaN blue LEDs were reported by Kim et al. [78,81, 146] and are summarized in Figure 18 (a-c). The LEDs were irradiated with protons at 340 keV and fluences of 5×10^{10} - 10^{14} cm^{-2} . Both current–voltage and light output–current characteristics were gradually degraded as increasing proton fluence. The reverse recovery time before and after 10^{14} cm^{-2} proton fluence decreased from 31.0 to 27.6 ns [78,81, 146]. Ion tracks in GaN-based devices have not been observed in LED structures and it will be interesting to see if the absence of a high electric field region still leads to the type of track observed in electronic devices with high reverse biases [147-151].

There has been less work on radiation damage in GaN-based lasers [145]. In general, it is found the threshold current increases with radiation fluence, with neutrons being more damaging than γ -rays because of higher effectiveness in producing

displacement defects. This increase is caused by nonradiative recombination centers competing with radiative recombination sites. Gamma irradiation does not cause significant degradation at doses lower than 10^7 - 10^8 rads if the irradiation is performed under lasing conditions. By contrast, neutron irradiation causes significant damage in GaN laser diodes at fluences $>10^{13}$ - 10^{14} cm^{-2} .

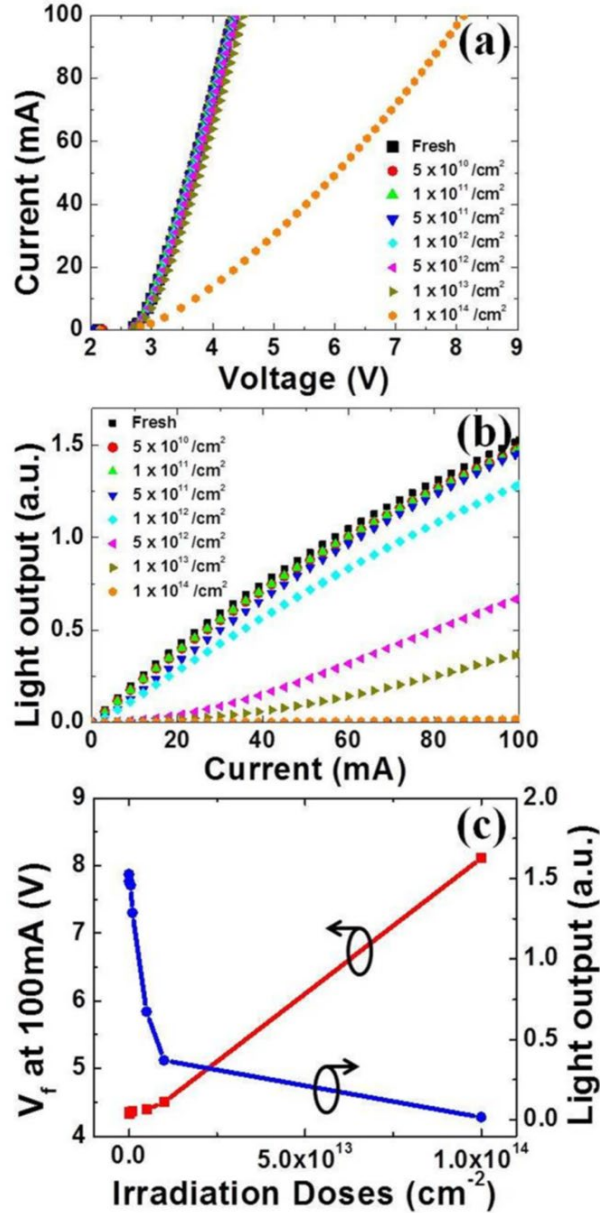


Figure 17. (Color online) (a) Current–voltage and (b) the light output–current characteristics of the InGaN/GaN blue LEDs prior to and after 340 keV proton irradiations with various doses, respectively. (c) The change of the forward voltage at an injection current of 100 mA and light output as a function of irradiation doses. Reprinted

6. SiC MOSFETs and BJTs

SiC devices have ten-fold higher breakdown field than Si devices. Thus, the drift layer within a SiC power device can be thinner or have higher doping levels. Commercial 4H-SiC power MOSFETs irradiated with gamma rays become inoperative after 300 kRad [152-160]. 4H-SiC power BJT suffered small gain degradation after a dose of 8.7 Mrad. Gamma rays usually produce little change in SiC devices without gate oxides, even up to 100 Mrad. This indicates that TID effects in the gate oxide are the dominant effect in gamma-exposed SiC devices, although SiC MOSFETs can be TID-robust, despite their relatively thick oxides. Typically, the currently available devices degrade at > 300 krad (Si).

Irradiation with protons, neutrons, and electrons creates displacement damage in SiC devices at high fluences [152-160]. Significant degradation in I-V characteristics of 6H-SiC transistors occurs for neutron fluences $> 5 \times 10^{15} \text{ cm}^{-2}$ [155-163].

SiC power MOSFETs are susceptible to heavy-ion irradiation induced SEB at ground level due to terrestrial neutrons. Figure 18 shows heavy ion induced single event burnout in a SiC diode [155]. Permanent changes in the mechanical properties of SiC can also be induced by ion bombardment [164].

The response to single event effects is the biggest issue with SiC power devices and their radiation stability. Some of the different SEEs in SiC Schottky diodes include transient effects due to charge injection, permanently increased leakage current and catastrophic burnout. These occur at different bias levels, as shown in Figure 19 [158,166-206]. The threshold for ion-induced leakage current and single-event burnout saturates with linear energy transfer (LET). SEB produces destructive failure and is electric field dependent. For example, 650 V-3300 V diodes fail at a similar fraction of rated V_R .

. Displacement damage to first order does not depend on field and occurs without biasing the device. If just the level of NIEL is considered during single event strikes, it would be predicted that a much lower amount of leakage current in SiC power devices per ion strike would be induced. The permanent damage occurring during these

catastrophic strikes also result from Joule heating along the ion track. TEM observations indicate the damage site diameter is approximately the same size as the ion track diameter [152-154]. The passage of these ion creates thermal damage, which has different effects to displacement damage. Experimentally, it is seen the degradation has little dependence on rated breakdown voltage. For example, 600 V-1700 V rectifiers all have the same critical power density threshold [158].

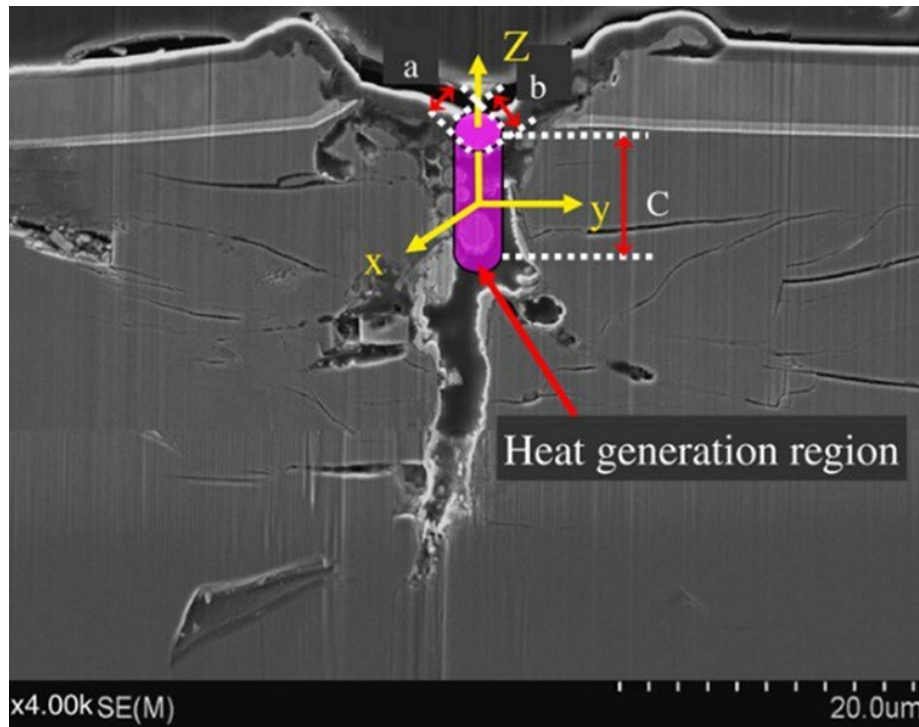


Figure 18. Heavy ion induced single event burnout in SiC diode. Reprinted with permission from Jpn. J. Appl. Phys., **53**, 04EP03, (2014). Copyright 2014 The Japan Society of Applied Physics.

In terms of single event burnout, the key components for SEB in SiC Schottky diodes have been identified via TCAD simulations. One important factor is the duration of high E-field at the Schottky contact [207-215], which impacts the onset of impact ionization and thermal runaway at the contact [154]. SEEs in SiC MOSFETs include latent gate damage, permanent increased leakage current, and formation of drain-gate or drain-source leakage pathways [210]. Drain-gate leakage is the main degradation in JFETs.

Gate damage in MOSFETs is minimized for lower LET or light ions. The mechanism suggested by Abbatte et al. [206, 207] is the ion strike causes a high field at the interface with the oxide, high hole trapping in oxide, a shift of SiC electric field across oxide, resulting in fast current injection. There is Poole-Frenkel-like rapid emission of holes from oxide traps and Fowler-Nordheim tunneling of holes across the SiC/SiO₂ interface. The SEB occurs at ~50% of rated bias. Figure 20 (a) shows degradation thresholds as functions of bias and LET, while experimental data is shown in Figure 20(b). Mitigating these risks is problematic if SEB protection circuitry is too slow to protect against ion-induced transients.

In SiC, heat removal is by acoustic phonons, but these take several ns to start conducting heat away. E-h pairs form along the track of the incoming ion, then optical phonons are created on a time scale of 1-5 ps. However, acoustic phonons to conduct heat away are not formed until ~1 ns [191,199, 209]. The higher high peak fields in SiC compared to Si means there is a two order of magnitude higher heat generation density. This leads to rapid rise in temperature, given by $\Delta T = \text{time} \times \text{power} / \text{heat capacity (C)}$, where $C \propto \text{heated volume}$. The expected temperature rises are beyond the melting point and SiC sublimation occurs in picoseconds [155,197, 199].

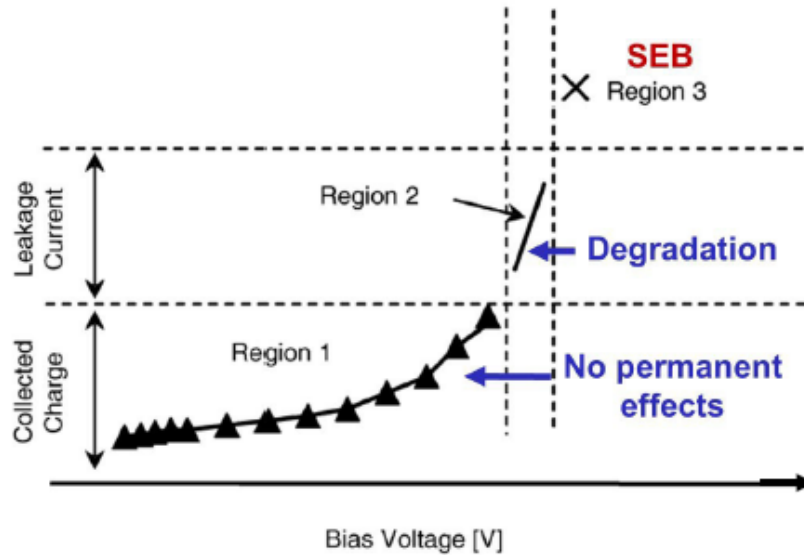


Figure 19. Characteristic regions observed by heavy ion irradiations on SiC Schottky diodes (The image was derived from experimental data with Ar ion). Reprinted with permission from IEEE T Nucl. Sci., **66**, 1688 (2019). Copyright 2019 IEEE.

To summarize SiC Schottky diode susceptibility to SEB occurs at $< 50\%$ of the rated avalanche bias. By sharp contrast, Si Schottky diodes do not fail at this bias level, with half passing at 100% . [158]. SEB occurs as a result of the faster recombination of electrons and holes at the high field contact [158]. The resulting lower carrier density increases the electric field at the contact and initiates impact ionization. The higher field is sustained for several hundred ps, inducing Joule heating which causes thermal runaway. The increased temperature causes more electron injection from the Schottky contact and recombination with holes. The positive feedback produces thermal runaway. Since the peak electric field in SiC power devices is an order of magnitude higher than in Si devices, the heat generation density in SiC devices is two orders of magnitude higher since the Joule power density is proportional to electric field squared. TCAD simulations indicate that thicker, lower doped, epitaxial layers increase the threshold for ion-induced SEB.

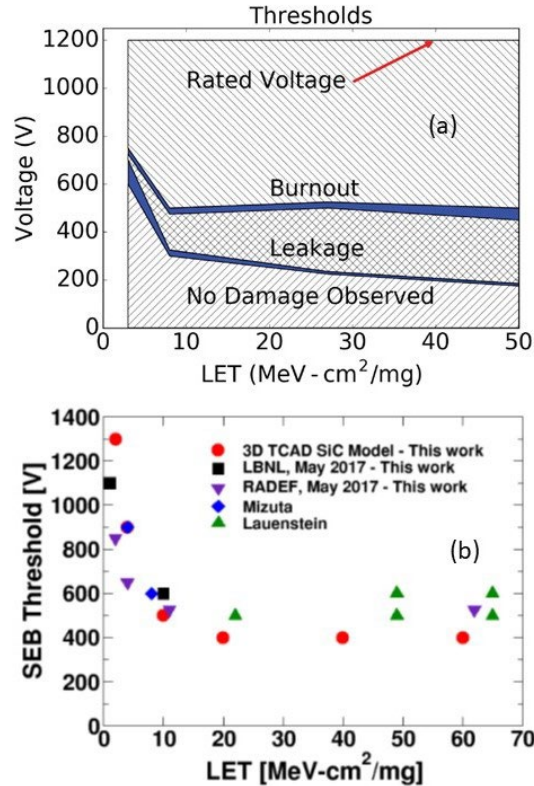


Figure 20. (a) Measured degradation mode thresholds as functions of applied bias and LET. The width of the line indicates minimum voltage at which burnout was observed and maximum voltage with no burnout. (b) SEB threshold voltage for 1.2 kV SiC

MOSFETs collected from several heavy-ion experiments. Adapted from J.-M. Lauenstein, Getting SiC Power Devices Off the Ground: Design, Testing, and Overcoming Radiation Threats, Microelectronics Reliability and Qualification Working (MRQW) Meeting, El Segundo, CA, February 2018.
<https://ntrs.nasa.gov/search.jsp?R=20180006113>.

Terrestrial neutron exposures of commercial SiC devices with planar, trench and double-trench architecture were found to produce different failure mechanisms [208].

In thesis work by Suvanam [218], studies were performed on radiation effects on MOS structures, 4H-SiC BJT, and 4H-SiC circuits using 50 keV Ar⁺, 3 MeV protons and gamma radiation. Radiation effects depended on the device structure and design and also on radiation dose. Compared to Si-technology [68] the 4H-SiC BJTs showed one order of magnitude higher radiation tolerances.

The radiation hardness of 4H-SiC bipolar junction transistor exposed to 332 Mrad gamma radiation and protons showed they were 100x more tolerant to gamma radiation than Si [216-219]. 4H-SiC devices and circuits irradiated with 3 MeV protons showed 10x higher tolerance compared to Si. For 4H SiC integrated OR-NOR logic circuits, no reduction in logic swing was observed to proton doses of 10¹² cm⁻² and gamma doses of 10⁸ Mrad. SiC BJTs irradiated with gamma rays showed recovery to 92% of the pre radiation condition after annealing at 420 °C for 1800 s [218].

In summary for SiC devices, there are still issues with stability of the SiC/SiO₂ interface in radiation environments. The main cause for degradation due to radiation is ionization effects in the dielectric and interface layers. The radiation stability is still 10-100x higher than Si.

7. Summary and Conclusions

The three main types of radiation effects, [220-227] TID, DD and SEE have different effects on SiC and GaN devices. In MOS devices, TID radiation creates traps in the oxide, which alters the local electric field at the interface with the semiconductor, and this can screen the externally applied voltage, changing the device operating characteristics. TID is due to the ionization created by the radiation as it passes through the semiconductor and dielectric. DD occurs when the incident atom has kinetic energy

higher than the displacement threshold energy of the semiconductor. Under these conditions, the incoming ion can displace lattice atoms, producing Frenkel pairs. The device parameters most sensitive to displacement damage are minority carrier lifetime, diffusion length, mobility and carrier concentration. The production rate of many traps observed in SiC and GaN after irradiation is directly proportional to energy loss per unit length of the incident ions due to displacement processes (NIEL). This shows they are due to atomic displacements.

SEE occur when an energetic particle traverses the semiconductor, producing electron-hole pairs along the track. While the e-h pairs recombine, they can produce a transient response in the device. Most of the SEEs disappear within picoseconds after the generated charges diffuse and recombine. While these are not destructive, if there is a high enough LET and strong electric fields are present at the device operating conditions, destructive mechanisms can occur.

Although these three types of damage are independent of each other, they obviously occur simultaneously during a radiation event [228]. As an example, a high energy proton will create electron-hole pairs while also displacing lattice atoms in the SiC or GaN lattice atoms. In other words, the same incoming ion and induce both TID and DD effects.

All commercially available SiC power devices, including Schottky and pin diodes, MOSFETs and JFETs show catastrophic single event-induced failure at $\leq 50\%$ of their rated voltages. The very high electric fields in such devices are the cause of failure at high ion LET values. There is also non-catastrophic damage at biases $\sim 10\%$ of rated values.

Photonic devices show changes in optical output intensity at lower radiation levels than those at which changes in the electrical parameters are noted. There has been little examination of using forward-bias injection of carriers to try to induce athermal annealing of radiation damage in GaN-based LEDs and lasers.

Overall, while SiC and GaN electronic devices are more robust against degradation by TID and DD effects during radiation exposure than Si devices, the current designs show a higher sensitivity to SEE, especially catastrophic burnout. Optimized design of active layer thicknesses and doping should partially mitigate these effects.

We can summarize the main conclusions as follows:

1. GaN and SiC devices are more resistant to total dose radiation damage than Si or GaAs, due to their higher bond strengths and higher defect recombination rates [2,15].
2. The wide bandgap devices are more susceptible to single event related failures due to the high electric fields present, which leads to thermal and electrical runaway. The only method to mitigate this involves operating them at lower than their rated voltages [2,163,195].
3. TID effects are usually only present in devices with MOS gates and thus this is significant in SiC MOSFETs [158,181,182]. GaN devices still mainly employ metal-gates and are relatively immune to ID effects.
4. Optimized design of devices that are specifically designed for improved radiation hardness will require significant investments in modelling and simulation [206,212]

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